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APPLICANT: Gormley et al.

GROUP: 2811

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EXAMINER: Hung K. Vu

FILED: September 14, 2000

FOR: A METHOD FOR FORMING A SEMICONDUCTOR DEVICE AND A  
SEMICONDUCTOR DEVICE FORMED BY THE METHOD

Assistant Commissioner of Patents  
Washington, D.C. 20231  
Box Non-Fee Amendment

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Sir:

AMENDMENT

In response to the Office Action mailed April 24, 2002, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

Page 12, line 14 delete "upper layer 26" and insert --upper surface 26--.

IN THE CLAIMS

Please amend claim 28 as follows:

- 1 28. (Amended) A method for forming a semiconductor device comprising at least a
- 2 first layer and a second layer with a component formed in the second layer, a first etch stop
- 3 layer being located between the first and second layers, and a second etch stop layer on the
- 4 second layer such that the second layer is located between the first and second etch stop layers,
- 5 the first etch stop layer being of depth greater than the second etch stop layer, the method
- 6 comprising the steps of:
- 7 prior to forming the component in the second layer forming a communicating bore
- 8 through the first layer [communicating with] to the first etch stop layer adjacent a portion of
- 9 the second layer where the component is to be formed, and